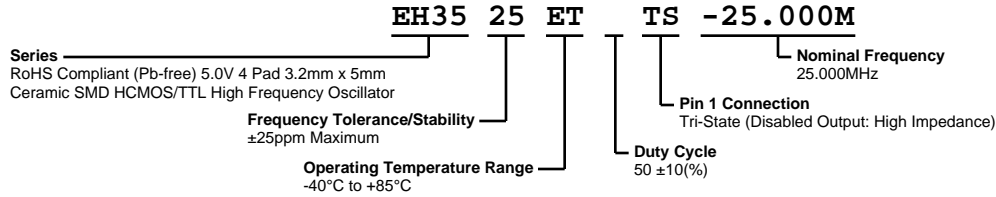


EH3525ETTS-25.000M



ECLIPTEK[®]
CORPORATION



ELECTRICAL SPECIFICATIONS

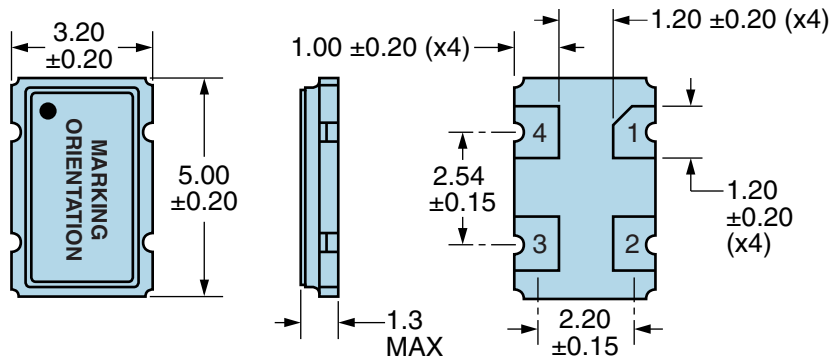
| | |
|--|--|
| Nominal Frequency | 25.000MHz |
| Frequency Tolerance/Stability | ±25ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration) |
| Aging at 25°C | ±5ppm/year Maximum |
| Operating Temperature Range | -40°C to +85°C |
| Supply Voltage | 5.0Vdc ±10% |
| Input Current | 50mA Maximum (No Load) |
| Output Voltage Logic High (Voh) | 2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH = -16mA) |
| Output Voltage Logic Low (Vol) | 0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL = +16mA) |
| Rise/Fall Time | 6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load or at 20% to 80% of waveform with HCMOS Load) |
| Duty Cycle | 50 ±10(%) (Measured at 1.4Vdc with TTL Load or at 50% of waveform with HCMOS Load) |
| Load Drive Capability | 10TTL Load or 50pF HCMOS Load Maximum |
| Output Logic Type | CMOS |
| Pin 1 Connection | Tri-State (Disabled Output: High Impedance) |
| Tri-State Input Voltage (Vih and Vil) | +2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output. |
| Absolute Clock Jitter | ±250pSec Maximum, ±100pSec Typical |
| One Sigma Clock Period Jitter | ±50pSec Maximum, ±30pSec Typical |
| Start Up Time | 10mSec Maximum |
| Storage Temperature Range | -55°C to +125°C |

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

| | |
|-------------------------------------|---------------------------------------|
| Fine Leak Test | MIL-STD-883, Method 1014, Condition A |
| Gross Leak Test | MIL-STD-883, Method 1014, Condition C |
| Mechanical Shock | MIL-STD-202, Method 213, Condition C |
| Resistance to Soldering Heat | MIL-STD-202, Method 210 |
| Resistance to Solvents | MIL-STD-202, Method 215 |
| Solderability | MIL-STD-883, Method 2003 |
| Temperature Cycling | MIL-STD-883, Method 1010 |
| Vibration | MIL-STD-883, Method 2007, Condition A |

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MECHANICAL DIMENSIONS (all dimensions in millimeters)



| PIN | CONNECTION |
|-----|--------------------|
| 1 | Tri-State |
| 2 | Ground/Case Ground |
| 3 | Output |
| 4 | Supply Voltage |

| LINE | MARKING |
|------|--|
| 1 | E25.000 <i>E=Ecliptek Designator</i> |

Suggested Solder Pad Layout

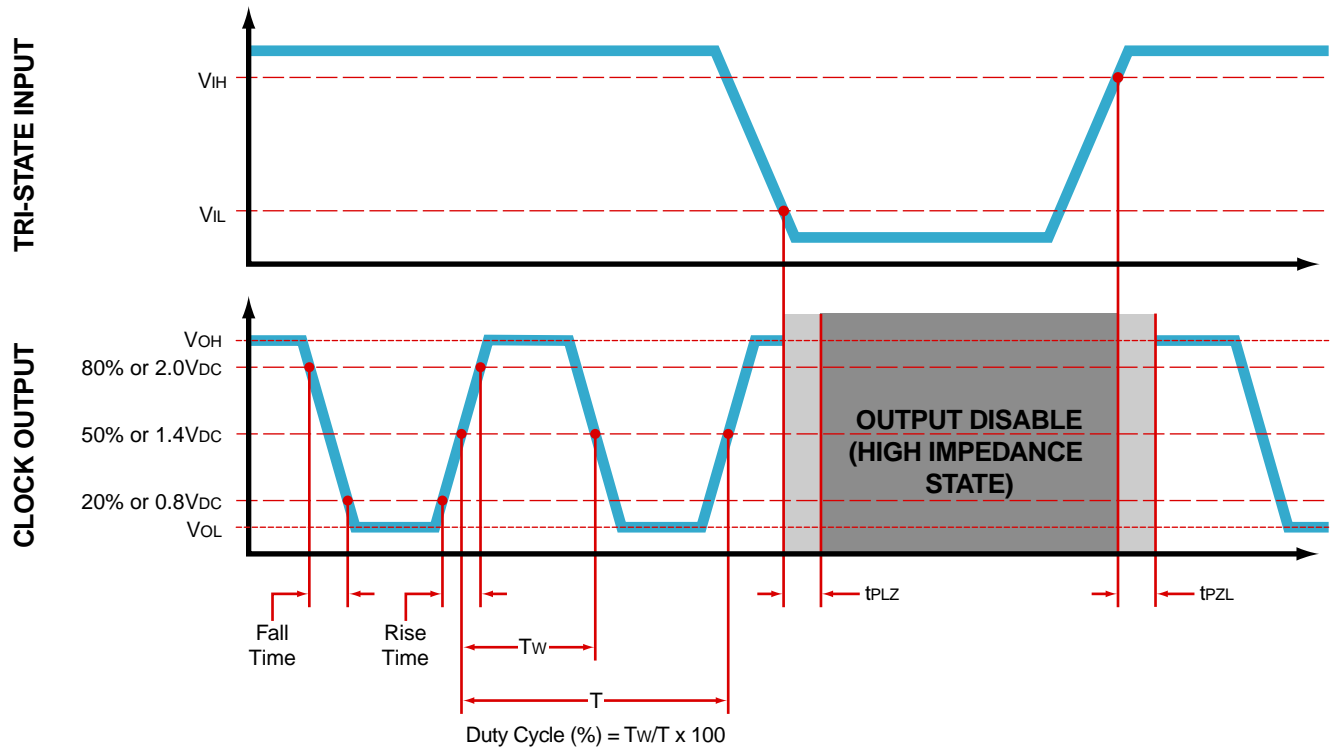
All Dimensions in Millimeters



All Tolerances are ±0.1

EH3525ETTS-25.000M

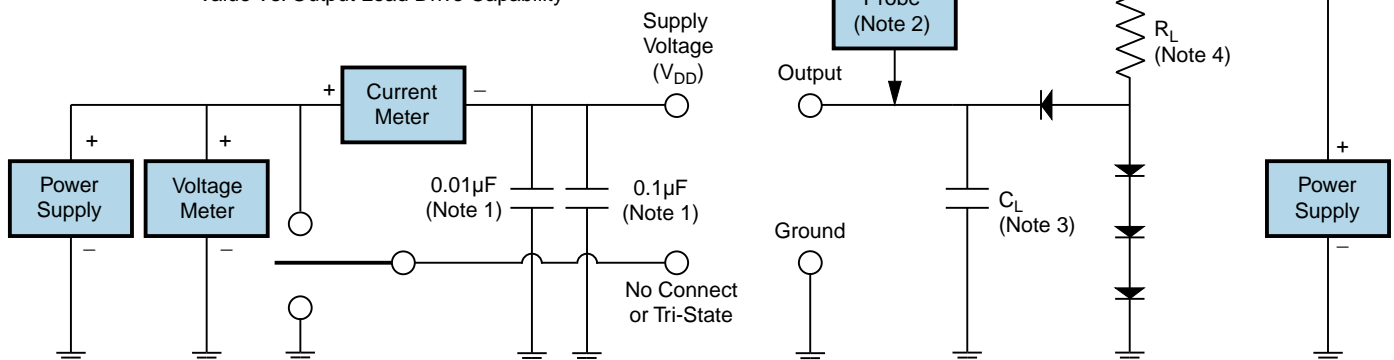
OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for TTL Output

| Output Load Drive Capability | R_L Value (Ohms) | C_L Value (pF) |
|------------------------------|--------------------|------------------|
| 10TTL | 390 | 15 |
| 5TTL | 780 | 15 |
| 2TTL | 1100 | 6 |
| 10LSTTL | 2000 | 15 |
| 1TTL | 2200 | 3 |

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability



- Note 1: An external 0.1 μ F low frequency tantalum bypass capacitor in parallel with a 0.01 μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.
- Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.
- Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

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Test Circuit for CMOS Output



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

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Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

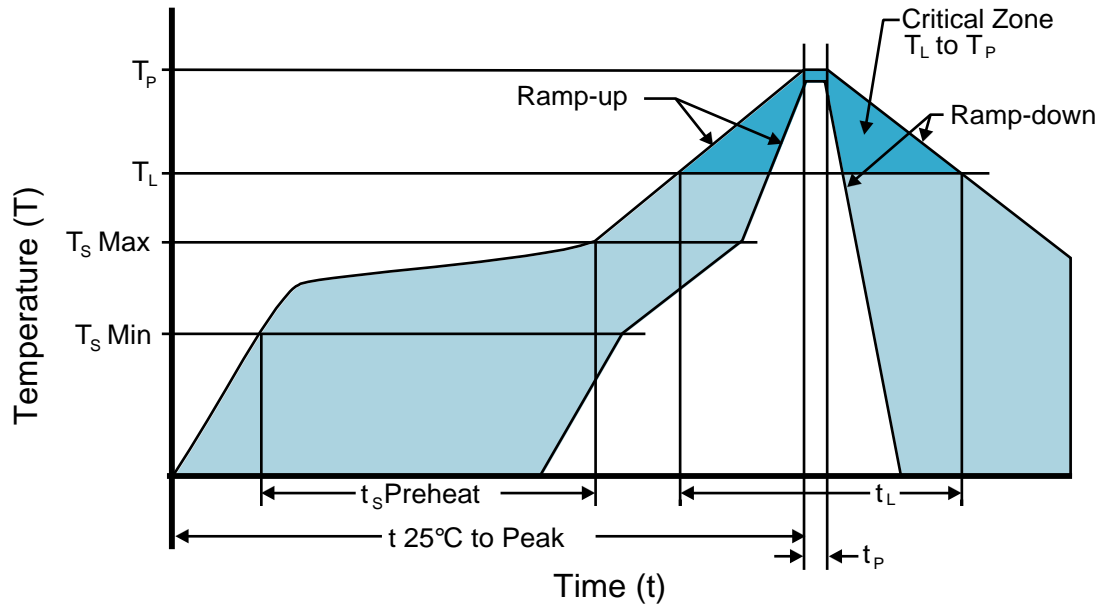
Recommended Solder Reflow Methods



High Temperature Infrared/Convection

| | |
|--|--------------------------------------|
| T_s MAX to T_L (Ramp-up Rate) | 3°C/second Maximum |
| Preheat | |
| - Temperature Minimum (T_s MIN) | 150°C |
| - Temperature Typical (T_s TYP) | 175°C |
| - Temperature Maximum (T_s MAX) | 200°C |
| - Time (t_s MIN) | 60 - 180 Seconds |
| Ramp-up Rate (T_L to T_p) | 3°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T_L) | 217°C |
| - Time (t_L) | 60 - 150 Seconds |
| Peak Temperature (T_p) | 260°C Maximum for 10 Seconds Maximum |
| Target Peak Temperature (T_p Target) | 250°C +0/-5°C |
| Time within 5°C of actual peak (t_p) | 20 - 40 seconds |
| Ramp-down Rate | 6°C/second Maximum |
| Time 25°C to Peak Temperature (t) | 8 minutes Maximum |
| Moisture Sensitivity Level | Level 1 |

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

| | |
|--|--|
| T_s MAX to T_L (Ramp-up Rate) | 5°C/second Maximum |
| Preheat | |
| - Temperature Minimum (T _s MIN) | N/A |
| - Temperature Typical (T _s TYP) | 150°C |
| - Temperature Maximum (T _s MAX) | N/A |
| - Time (t _s MIN) | 60 - 120 Seconds |
| Ramp-up Rate (T_L to T_P) | 5°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T _L) | 150°C |
| - Time (t _L) | 200 Seconds Maximum |
| Peak Temperature (T_P) | 240°C Maximum |
| Target Peak Temperature (T_P Target) | 240°C Maximum 1 Time / 230°C Maximum 2 Times |
| Time within 5°C of actual peak (t_p) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate | 5°C/second Maximum |
| Time 25°C to Peak Temperature (t) | N/A |
| Moisture Sensitivity Level | Level 1 |

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.